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Embedded LPDDR2 SDRAM

EDB1316BD, EDB1332BD, EDB2432B4, EDB4064B4

Features

- Ultra low-voltage core and I/O power supplies
 - $V_{DD2} = 1.14\text{--}1.30\text{V}$
 - $V_{DDCA}/V_{DDQ} = 1.14\text{--}1.30\text{V}$
 - $V_{DD1} = 1.70\text{--}1.95\text{V}$
- Clock frequency range
 - 533–10 MHz (data rate range: 1066–20 Mb/s/pin)
- Four-bit prefetch DDR architecture
- Eight internal banks for concurrent operation
- Multiplexed, double data rate, command/address inputs; commands entered on every CK edge
- Bidirectional/differential data strobe per byte of data (DQS/DQS#)
- Programmable READ and WRITE latencies (RL/WL)
- Programmable burst lengths: 4, 8, or 16
- Per-bank refresh for concurrent operation
- Partial-array self refresh (PASR)
- Deep power-down mode (DPD)
- Selectable output drive strength (DS)
- Clock stop capability
- RoHS-compliant, “green” packaging

Table 1: Key Timing Parameters

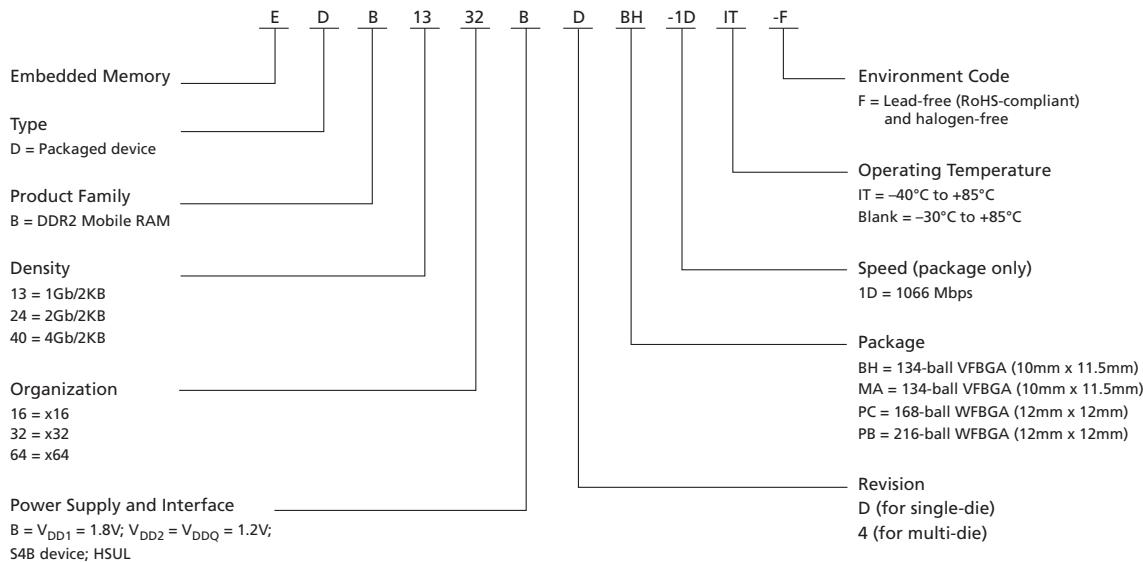
Speed Grade	Clock Rate (MHz)	Data Rate (Mb/s/pin)	RL	WL
1D	533	1066	8	4

Options	Marking
• Density/Page Size <ul style="list-style-type: none"> – 1Gb/2KB - single die – 2Gb/2KB - dual die – 4Gb/2KB - quad die 	13 24 40
• Organization <ul style="list-style-type: none"> – x16 – x32 – x64 	16 32 64
• V_{DD2} : 1.2V	B
• Revision <ul style="list-style-type: none"> – Single die – Multi-die 	D 4
• FBGA “green” package <ul style="list-style-type: none"> – 134-ball FBGA – 134-ball multi-die FBGA – 168-ball FBGA for PoP – 216-ball multi-die FBGA for PoP 	BH MA PC PB
• Timing – cycle time <ul style="list-style-type: none"> – 1.875ns @ RL = 8 	-1D
• Operating temperature range <ul style="list-style-type: none"> – From -30°C to $+85^\circ\text{C}$ – From -40°C to $+85^\circ\text{C}$ 	(Blank) IT

Table 2: S4 Configuration Addressing

Architecture	64 Meg x 16	32 Meg x 32	64 Meg x 32	64 Meg x 64
Die configuration	8 Meg x 16 x 8 banks	4 Meg x 32 x 8 banks	2 x 8 Meg x 16 x 8 banks	4 x 8 Meg x 16 x 8 banks
Row addressing	8K (A[12:0])	8K (A[12:0])	8K (A[12:0])	8K (A[12:0])
Column addressing	1K (A[9:0])	512 (A[8:0])	1K (A[9:0])	1K (A[9:0])
Number of die	1	1	2	4
Die per rank	1	1	2	2
Ranks per channel ¹	1	1	1	2

Note: 1. A channel is a complete LPDRAM interface, including command/address and data pins.

Figure 1: LPDDR2 Part Numbering


FBGA Part Marking Decoder

Due to space limitations, FBGA-packaged components have an abbreviated part marking that is different from the part number. Micron's FBGA part marking decoder is available at www.micron.com/decoder.

Table 3: Package Codes and Descriptions

Package Code	Ball Count	# Ranks	# Channels	Size (mm)	Die per Package	Solder Ball Composition
BH	134	1	1	10 x 11.5 x 1.0, 0.65 pitch	SDP	SAC302
MA	134	1	1	10 x 11.5 x 1.0, 0.65 pitch	DDP	SAC302
PC	168	1	1	12 x 12 x 0.8, 0.5 pitch	SDP	SAC302
PB	216	2	2	12 x 12 x 0.8, 0.4 pitch	QDP	SAC302

Notes:

1. SDP = single-die package; DDP = Dual-die package; QDP = Quad-die package;.
2. Solder ball material: SAC302 (96.8% Sn, 3% Ag, 0.2% Cu).

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General Description

The Low-Power DDR2 SDRAM (LPDDR2) is a high-speed CMOS, dynamic random-access memory containing 1,073,741,824 bits. The LPDDR2-S4 device is internally configured as an eight-bank DRAM. Each of the x16's 134,217,728-bit banks is organized as 8192 rows by 1024 columns by 16 bits. Each of the x32's 134,217,728-bit banks is organized as 8192 rows by 512 columns by 32 bits.

General Notes

Throughout the data sheet, figures and text refer to DQs as "DQ." DQ should be interpreted as any or all DQ collectively, unless specifically stated otherwise.

"DQS" and "CK" should be interpreted as DQS, DQS# and CK, CK# respectively, unless specifically stated otherwise. "BA" includes all BA pins used for a given density.

In timing diagrams, "CMD" is used as an indicator only. Actual signals occur on CA[9:0].

V_{REF} indicates V_{REFCA} and V_{REFDQ}.

Complete functionality may be described throughout the entire document. Any page or diagram may have been simplified to convey a topic and may not be inclusive of all requirements.

Any specific requirement takes precedence over a general statement.

Any functionality not specifically stated herein is considered undefined, illegal, is not supported, and will result in unknown operation.

I_{DD} Specifications

Table 4: I_{DD} Specifications (32 Meg x 32)

V_{DD2}, V_{DDQ}, V_{DDCA} = 1.14–1.30V; V_{DD1} = 1.70–1.95V

Parameter	Supply	Speed Grade	Unit
		-1D	
I _{DD01}	V _{DD1}	6	mA
I _{DD02}	V _{DD2}	30	
I _{DD0,in}	V _{DDCA} + V _{DDQ}	1	
I _{DD2P1}	V _{DD1}	600	μA
I _{DD2P2}	V _{DD2}	1600	
I _{DD2P,in}	V _{DDCA} + V _{DDQ}	100	
I _{DD2PS1}	V _{DD1}	600	μA
I _{DD2PS2}	V _{DD2}	1600	
I _{DD2PS,in}	V _{DDCA} + V _{DDQ}	100	
I _{DD2N1}	V _{DD1}	0.6	mA
I _{DD2N2}	V _{DD2}	20	
I _{DD2N,in}	V _{DDCA} + V _{DDQ}	1	
I _{DD2NS1}	V _{DD1}	0.6	mA
I _{DD2NS2}	V _{DD2}	12	
I _{DD2NS,in}	V _{DDCA} + V _{DDQ}	1	
I _{DD3P1}	V _{DD1}	1.4	mA
I _{DD3P2}	V _{DD2}	5	
I _{DD3P,in}	V _{DDCA} + V _{DDQ}	0.1	
I _{DD3PS1}	V _{DD1}	1.4	mA
I _{DD3PS2}	V _{DD2}	5	
I _{DD3PS,in}	V _{DDCA} + V _{DDQ}	0.1	
I _{DD3N1}	V _{DD1}	1.5	mA
I _{DD3N2}	V _{DD2}	22	
I _{DD3N,in}	V _{DDCA} + V _{DDQ}	1	
I _{DD3NS1}	V _{DD1}	1.5	mA
I _{DD3NS2}	V _{DD2}	14	
I _{DD3NS,in}	V _{DDCA} + V _{DDQ}	1	
I _{DD4R1}	V _{DD1}	2	mA
I _{DD4R2}	V _{DD2}	180	
I _{DD4R,in}	V _{DDCA}	2	
I _{DD4W1}	V _{DD1}	2	mA
I _{DD4W2}	V _{DD2}	200	
I _{DD4W,in}	V _{DDCA} + V _{DDQ}	1	

Table 4: I_{DD} Specifications (32 Meg x 32) (Continued)

V_{DD2}, V_{DDQ}, V_{DDCA} = 1.14–1.30V; V_{DD1} = 1.70–1.95V

Parameter	Supply	Speed Grade	Unit
		-1D	
I _{DD51}	V _{DD1}	20	mA
I _{DD52}	V _{DD2}	70	
I _{DD5,in}	V _{DDCA} + V _{DDQ}	1	
I _{DD5PB1}	V _{DD1}	2	mA
I _{DD5PB2}	V _{DD2}	23	
I _{DD5PB,in}	V _{DDCA} + V _{DDQ}	1	
I _{DD5AB1}	V _{DD1}	2	mA
I _{DD5AB2}	V _{DD2}	23	
I _{DD5AB,in}	V _{DDCA} + V _{DDQ}	1	
I _{DD81}	V _{DD1}	50	μA
I _{DD82}	V _{DD2}	50	
I _{DD8,in}	V _{DDCA} + V _{DDQ}	20	

Table 5: I_{DD} Specifications (64 Meg x 16)

V_{DD2}, V_{DDQ}, V_{DDCA} = 1.14–1.30V; V_{DD1} = 1.70–1.95V

Parameter	Supply	Speed Grade	Unit
		-1D	
I _{DD01}	V _{DD1}	6	mA
I _{DD02}	V _{DD2}	30	
I _{DD0,in}	V _{DDCA} + V _{DDQ}	1	
I _{DD2P1}	V _{DD1}	600	μA
I _{DD2P2}	V _{DD2}	1600	
I _{DD2P,in}	V _{DDCA} + V _{DDQ}	100	
I _{DD2PS1}	V _{DD1}	600	μA
I _{DD2PS2}	V _{DD2}	1600	
I _{DD2PS,in}	V _{DDCA} + V _{DDQ}	100	
I _{DD2N1}	V _{DD1}	0.6	mA
I _{DD2N2}	V _{DD2}	20	
I _{DD2N,in}	V _{DDCA} + V _{DDQ}	1	
I _{DD2NS1}	V _{DD1}	0.6	mA
I _{DD2NS2}	V _{DD2}	12	
I _{DD2NS,in}	V _{DDCA} + V _{DDQ}	1	
I _{DD3P1}	V _{DD1}	1.4	mA
I _{DD3P2}	V _{DD2}	5	
I _{DD3P,in}	V _{DDCA} + V _{DDQ}	0.1	

Table 5: I_{DD} Specifications (64 Meg x 16) (Continued)

V_{DD2}, V_{DDQ}, V_{DDCA} = 1.14–1.30V; V_{DD1} = 1.70–1.95V

Parameter	Supply	Speed Grade	Unit
		-1D	
I _{DD3PS1}	V _{DD1}	1.4	mA
I _{DD3PS2}	V _{DD2}	5	
I _{DD3PS,in}	V _{DDCA} + V _{DDQ}	0.1	
I _{DD3N1}	V _{DD1}	1.5	mA
I _{DD3N2}	V _{DD2}	22	
I _{DD3N,in}	V _{DDCA} + V _{DDQ}	1	
I _{DD3NS1}	V _{DD1}	1.5	mA
I _{DD3NS2}	V _{DD2}	14	
I _{DD3NS,in}	V _{DDCA} + V _{DDQ}	1	
I _{DD4R1}	V _{DD1}	2	mA
I _{DD4R2}	V _{DD2}	140	
I _{DD4R,in}	V _{DDCA}	2	
I _{DD4W1}	V _{DD1}	2	mA
I _{DD4W2}	V _{DD2}	155	
I _{DD4W,in}	V _{DDCA} + V _{DDQ}	1	
I _{DD51}	V _{DD1}	20	mA
I _{DD52}	V _{DD2}	70	
I _{DD5,in}	V _{DDCA} + V _{DDQ}	1	
I _{DD5PB1}	V _{DD1}	2	mA
I _{DD5PB2}	V _{DD2}	23	
I _{DD5PB,in}	V _{DDCA} + V _{DDQ}	1	
I _{DD5AB1}	V _{DD1}	2	mA
I _{DD5AB2}	V _{DD2}	23	
I _{DD5AB,in}	V _{DDCA} + V _{DDQ}	1	
I _{DD81}	V _{DD1}	50	μA
I _{DD82}	V _{DD2}	50	
I _{DD8,in}	V _{DDCA} + V _{DDQ}	20	

Table 6: I_{DD} Specifications (64 Meg x 32, 64 Meg x 64¹)

V_{DD}, V_{DDQ}, V_{DDCA} = 1.14–1.30V; V_{DD1} = 1.70–1.95V

Parameter	Supply	Speed Grade	Unit
		-1D	
I _{DD01}	V _{DD1}	12	mA
I _{DD02}	V _{DD2}	60	
I _{DD0,in}	V _{DDCA} + V _{DDQ}	2	

Table 6: I_{DD} Specifications (64 Meg x 32, 64 Meg x 64¹) (Continued)

V_{DD}, V_{DDQ}, V_{DDCA} = 1.14–1.30V; V_{DD1} = 1.70–1.95V

Parameter	Supply	Speed Grade	Unit
		-1D	
I _{DD2P1}	V _{DD1}	1200	μA
I _{DD2P2}	V _{DD2}	3200	
I _{DD2P,in}	V _{DDCA} + V _{DDQ}	200	
I _{DD2PS1}	V _{DD1}	1200	μA
I _{DD2PS2}	V _{DD2}	3200	
I _{DD2PS,in}	V _{DDCA} + V _{DDQ}	200	
I _{DD2N1}	V _{DD1}	1.2	mA
I _{DD2N2}	V _{DD2}	40	
I _{DD2N,in}	V _{DDCA} + V _{DDQ}	2	
I _{DD2NS1}	V _{DD1}	1.2	mA
I _{DD2NS2}	V _{DD2}	24	
I _{DD2NS,in}	V _{DDCA} + V _{DDQ}	2	
I _{DD3P1}	V _{DD1}	2.8	mA
I _{DD3P2}	V _{DD2}	10	
I _{DD3P,in}	V _{DDCA} + V _{DDQ}	0.2	
I _{DD3PS1}	V _{DD1}	2.8	mA
I _{DD3PS2}	V _{DD2}	10	
I _{DD3PS,in}	V _{DDCA} + V _{DDQ}	0.2	
I _{DD3N1}	V _{DD1}	3	mA
I _{DD3N2}	V _{DD2}	44	
I _{DD3N,in}	V _{DDCA} + V _{DDQ}	2	
I _{DD3NS1}	V _{DD1}	3	mA
I _{DD3NS2}	V _{DD2}	28	
I _{DD3NS,in}	V _{DDCA} + V _{DDQ}	2	
I _{DD4R1}	V _{DD1}	4	mA
I _{DD4R2}	V _{DD2}	280	
I _{DD4R,in}	V _{DDCA}	4	
I _{DD4W1}	V _{DD1}	4	mA
I _{DD4W2}	V _{DD2}	310	
I _{DD4W,in}	V _{DDCA} + V _{DDQ}	2	
I _{DD51}	V _{DD1}	40	mA
I _{DD52}	V _{DD2}	140	
I _{DD5,in}	V _{DDCA} + V _{DDQ}	2	
I _{DD5PB1}	V _{DD1}	4	mA
I _{DD5PB2}	V _{DD2}	46	
I _{DD5PB,in}	V _{DDCA} + V _{DDQ}	2	

Table 6: I_{DD} Specifications (64 Meg x 32, 64 Meg x 64¹) (Continued)

V_{DD}, V_{DDQ}, V_{DDCA} = 1.14–1.30V; V_{DD1} = 1.70–1.95V

Parameter	Supply	Speed Grade	Unit
		-1D	
I _{DD5AB1}	V _{DD1}	4	mA
I _{DD5AB2}	V _{DD2}	46	
I _{DD5AB,in}	V _{DDCA} + V _{DDQ}	2	
I _{DD81}	V _{DD1}	100	μA
I _{DD82}	V _{DD2}	100	
I _{DD8,in}	V _{DDCA} + V _{DDQ}	40	

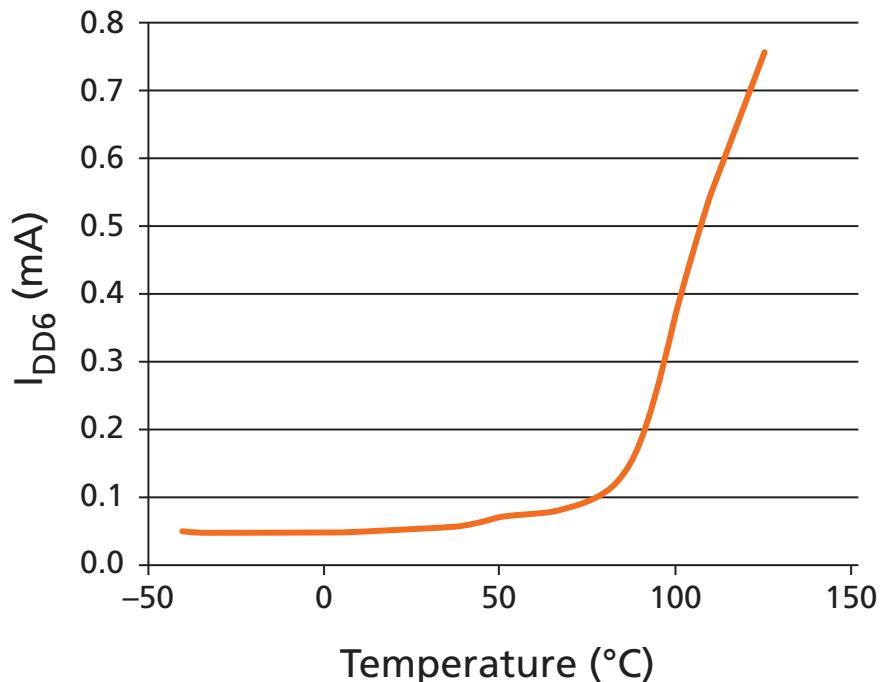
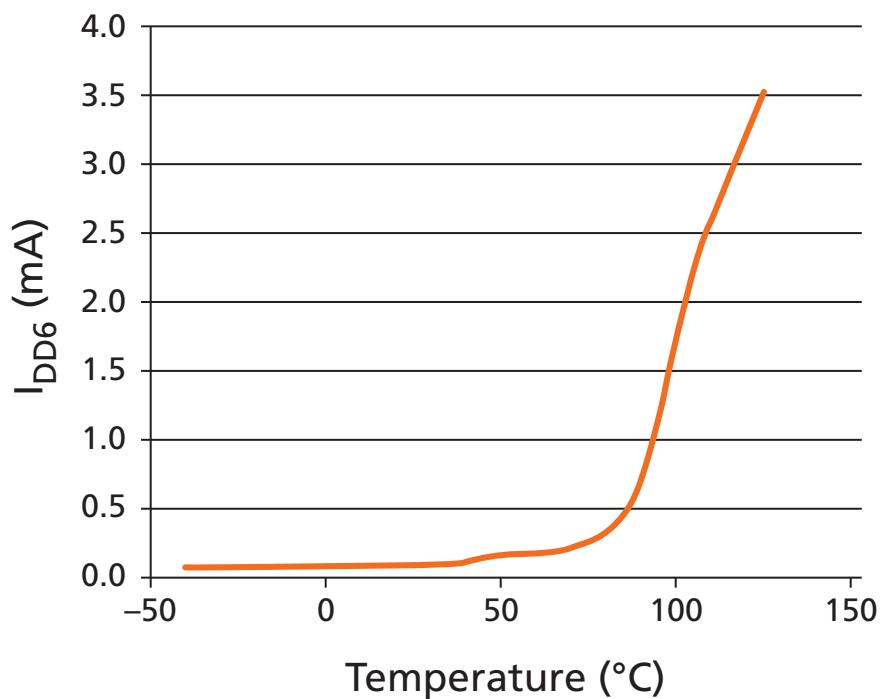
Note: 1. Actual I_{DD} for the 64M x 64 QDP device is dependant on the specific states in which the memory controller operates each of the two ranks. Consult Micron's Power Calculator for LPDDR2.

Table 7: I_{DD6} Partial-Array Self Refresh Current

V_{DD2}, V_{DDQ}, V_{DDCA} = 1.14–1.30V; V_{DD1} = 1.70–1.95V

PASR	Supply	I _{DD6} Partial-Array Self Refresh Current			Unit
		32 Meg x 32	64 Meg x 16	64 Meg x 32	
Full array	V _{DD1}	230		460	μA
	V _{DD2}	700		1400	
	V _{DDi}	20		40	
1/2 array	V _{DD1}	200		400	
	V _{DD2}	500		1000	
	V _{DDi}	20		40	
1/4 array	V _{DD1}	190		380	
	V _{DD2}	400		800	
	V _{DDi}	20		40	
1/8 array	V _{DD1}	185		370	
	V _{DD2}	360		720	
	V _{DDi}	20		40	

Note: 1. LPDDR2-S4 SDRAM devices support both bank-masking and segment-masking. I_{DD6} PASR currents are measured using bank-masking only.

Figure 2: V_{DD1} Typical Self-Refresh Current vs. Temperature (Per Die)**Figure 3: V_{DD2} Typical Self-Refresh Current vs. Temperature (Per Die)**

Package Block Diagrams

Figure 4: Single Die Single Rank, Single Channel Package Block Diagram

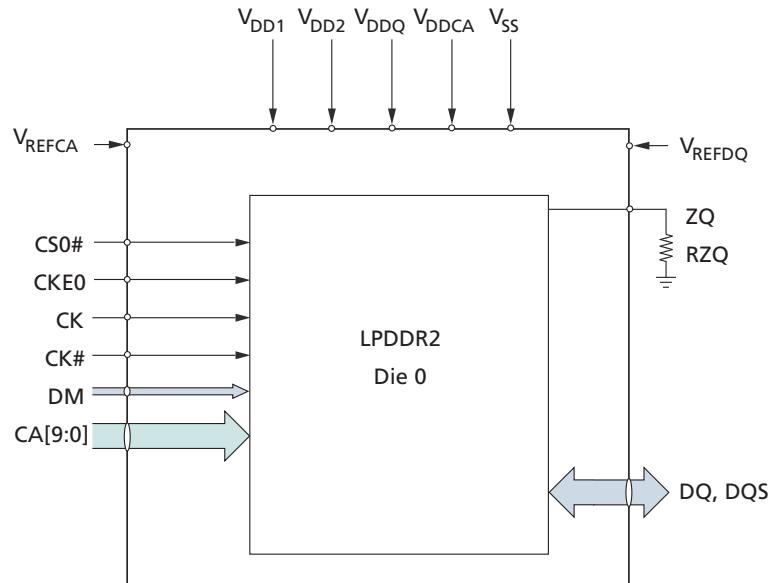


Figure 5: Dual Die Single Rank, Single Channel Package Block Diagram

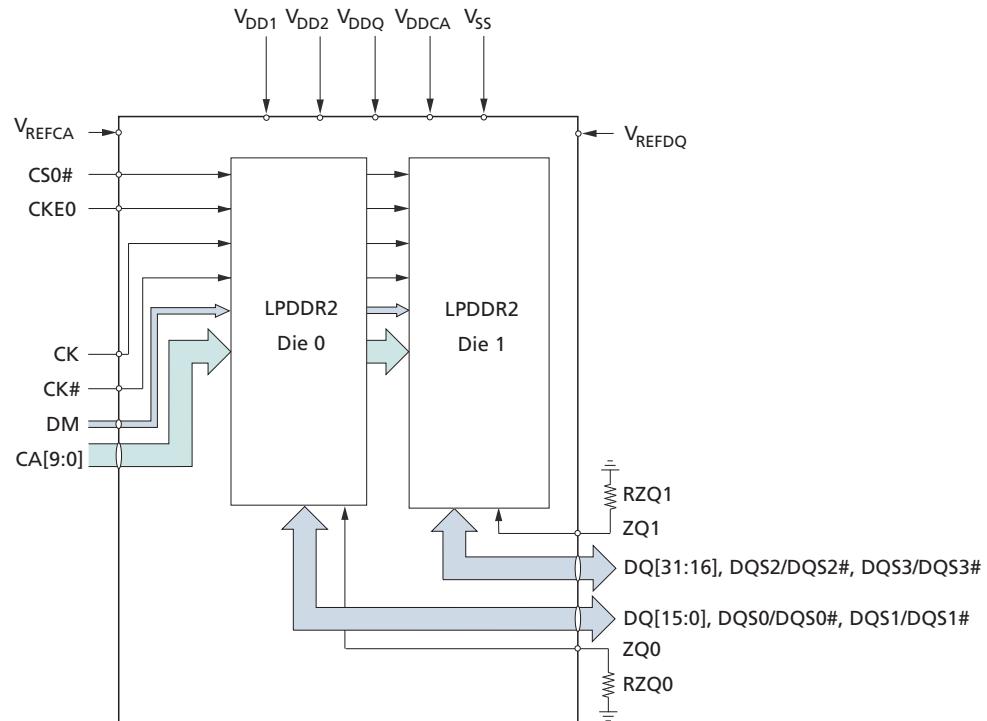
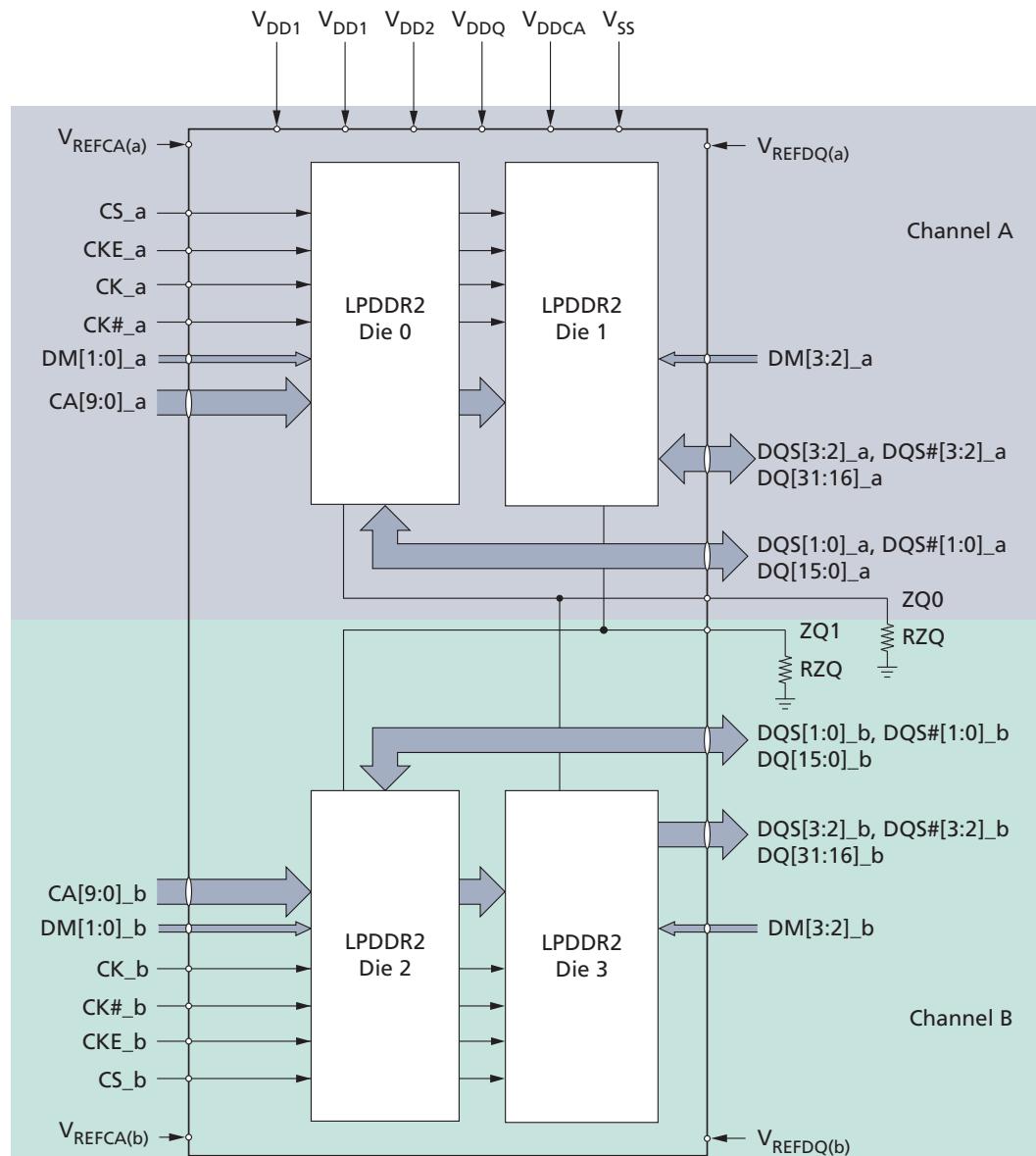
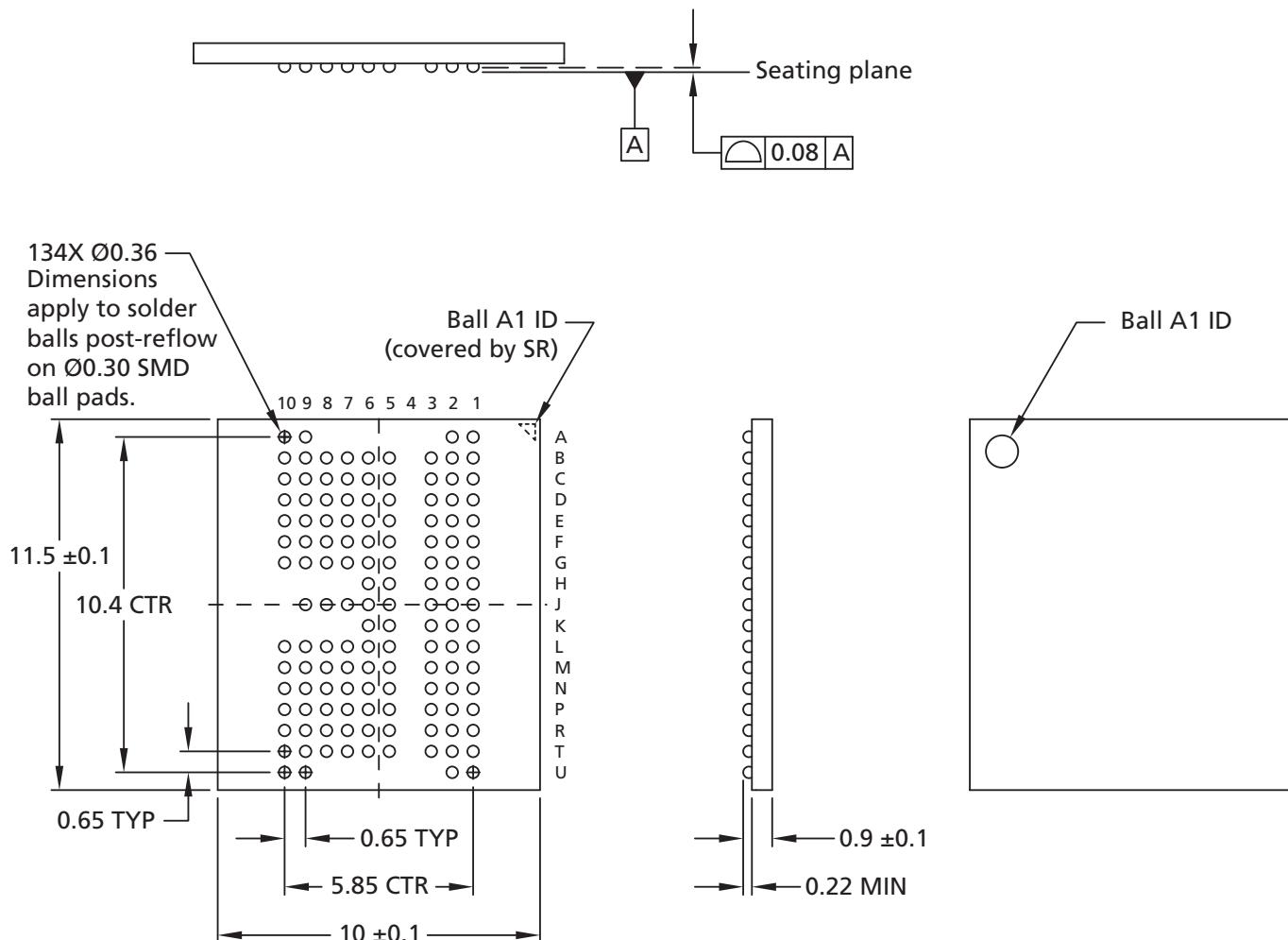


Figure 6: Quad Die Dual Rank, Dual Channel Package Block Diagram


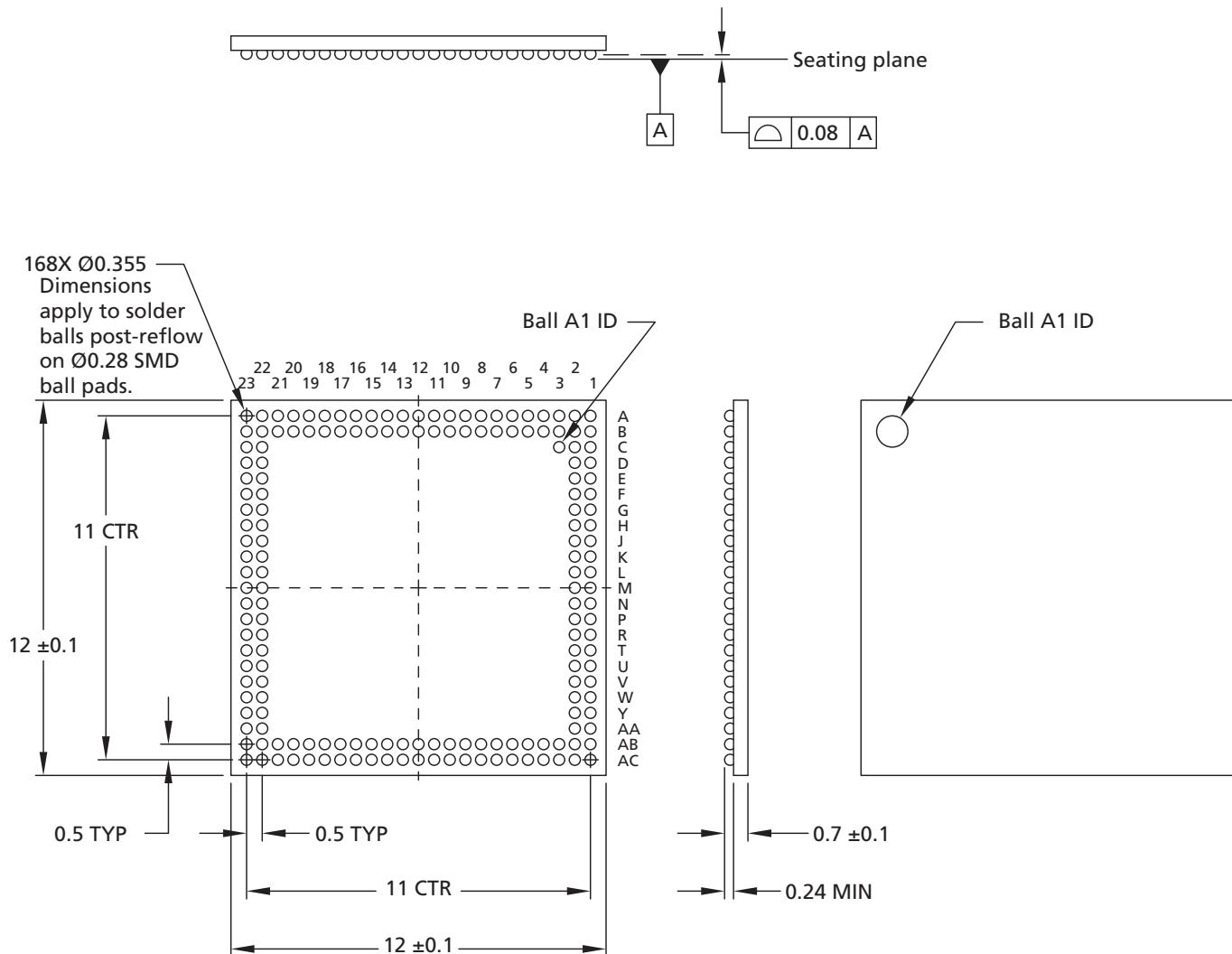
Package Dimensions

Figure 7: 134-Ball VFBGA – 10mm x 11.5mm (Package Code: BH, MA)



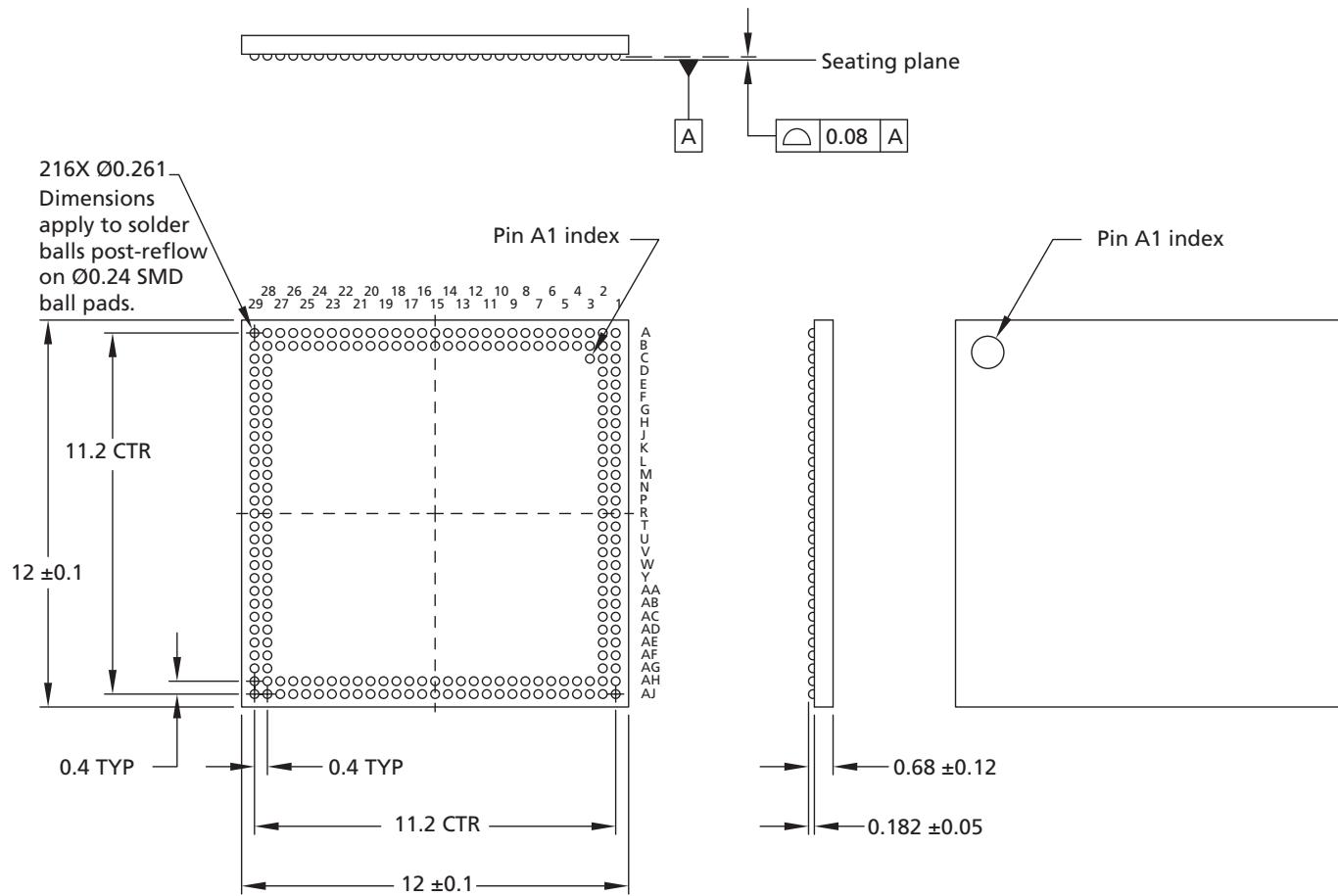
Note: 1. All dimensions are in millimeters.

Figure 8: 168-Ball WFBGA – 12mm x 12mm (Package Code: PC)



Note: 1. All dimensions are in millimeters.

Figure 9: 216-Ball WFBGA – 12mm x 12mm (Package Code: PB)



Note: 1. All dimensions are in millimeters.

Ball Assignments

Figure 10: 134-Ball FBGA (x16)

	1	2	3	4	5	6	7	8	9	10	
A	DNU	DNU							DNU	DNU	A
B	DNU	NC	NC								B
C	V _{DD1}	V _{SS}	RFU								C
D	V _{SS}	V _{DD2}	ZQ0								D
E	V _{SSCA}	CA9	CA8								E
F	V _{DDCA}	CA6	CA7								F
G	V _{DD2}	CA5	V _{REFCA}								G
H	V _{DDCA}	V _{SS}	CK#								H
J	V _{SSCA}	NC	CK								J
K	CKE0	RFU	RFU								K
L	CS0#	RFU	RFU								L
M	CA4	CA3	CA2								M
N	V _{SSCA}	V _{DDCA}	CA1								N
P	V _{SS}	V _{DD2}	CA0								P
R	V _{DD1}	V _{SS}	NC								R
T	DNU	NC	NC								T
U	DNU	DNU							DNU	DNU	U
	1	2	3	4	5	6	7	8	9	10	

Top View (ball down)

Note: 1. V_{DDCA} is unnecessary. F1, H1, and N2 pins should be left unconnected.

Figure 11: 134-Ball FBGA (x32)

	1	2	3	4	5	6	7	8	9	10	
A	DNU	DNU							DNU	DNU	A
B	DNU	NC	NC								B
C	V _{DD1}	V _{SS}	ZQ1								C
D	V _{SS}	V _{DD2}	ZQ0								D
E	V _{SSCA}	CA9	CA8								E
F	V _{DDCA}	CA6	CA7								F
G	V _{DD2}	CA5	V _{REFCA}								G
H	V _{DDCA}	V _{SS}	CK#								H
J	V _{SSCA}	NC	CK								J
K	CKE0	RFU	RFU								K
L	CS0#	RFU	RFU								L
M	CA4	CA3	CA2								M
N	V _{SSCA}	V _{DDCA}	CA1								N
P	V _{SS}	V _{DD2}	CA0								P
R	V _{DD1}	V _{SS}	NC								R
T	DNU	NC	NC								T
U	DNU	DNU							DNU	DNU	U

1 2 3 4 5 6 7 8 9 10

Top View (ball down)

Notes:

1. V_{DDCA} is unnecessary. F1, H1, and N2 pins should be left unconnected.
2. C3 pin is RFU for 32 Meg x 32 and ZQ1 for 64 Meg x 32.

Figure 12: 168-Ball FBGA

	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	
A	DNU	DNU	NC	NC	NC	(NC) ²	NC	NC	(NC) ²	NC	V _{DD1}	V _{SSQ}	DQ30	DQ29	V _{SSQ}	DQ26	DQ25	V _{SSQ}	DQS#3	V _{DD1}	V _{SS}	DNU	DNU	A
B	DNU	DNU	V _{DD1}	NC	NC	NC	NC	NC	NC	V _{SS}	V _{DD2}	DQ31	DQ28	DQ27	V _{DDQ}	DQ24	DQS3	V _{DDQ}	DM3	V _{DD2}	DNU	DNU	B	
C	V _{SS}	V _{DD2}																			DQ15	V _{SSQ}		C
D	NC	NC																			V _{DDQ}	DQ14		D
E	NC	NC																			DQ12	DQ13		E
F	(NC) ²	NC																			DQ11	V _{SSQ}		F
G	NC	NC																			V _{DDQ}	DQ10		G
H	NC	NC																		DQ8	DQ9		H	
J	(NC) ²	NC																		DQS1	V _{SSQ}		J	
K	NC	NC																		V _{DDQ}	DQS#1		K	
L	NC	NC																		V _{DD2}	DM1		L	
M	NC	V _{SS}																		V _{REFDQ}	V _{SS}		M	
N	NC	V _{DD1}																		V _{DD1}	DM0		N	
P	ZQ	V _{REFCA}																		DQS#0	V _{SSQ}		P	
R	V _{SS}	V _{DD2}																		V _{DDQ}	DQS0		R	
T	CA9	CA8																		DQ6	DQ7		T	
U	CA7	V _{DDCA}																		DQ5	V _{SSQ}		U	
V	V _{SSCA}	CA6																		V _{DDQ}	DQ4		V	
W	CA5	V _{DDCA}																		DQ2	DQ3		W	
Y	CK#	CK																		DQ1	V _{SSQ}		Y	
AA	V _{SS}	V _{DD2}																		V _{DDQ}	DQ0		AA	
AB	DNU	DNU	CS0#	RFU	V _{DD1}	CA1	V _{SSCA}	CA3	CA4	V _{DD2}	V _{SS}	DQ16	V _{DDQ}	DQ18	DQ20	V _{DDQ}	DQ22	DQS2	V _{DDQ}	DM2	V _{DD2}	DNU	DNU	AB
AC	DNU	DNU	CKE0	RFU	V _{SS}	CA0	CA2	V _{DDCA}	V _{SS} ¹	(NC) ²	NC	V _{SSQ}	DQ17	DQ19	V _{SSQ}	DQ21	DQ23	V _{SSQ}	DQS#2	V _{DD1}	V _{SS}	DNU	DNU	AC

Top View (ball down)

LPDDR2
Supply
Ground

- Notes:
1. Ball AC9 may be V_{SS} or left unconnected.
 2. Balls labeled "(NC)" = no connect; however, they can be connected together internally.
 3. V_{DDCA} is unnecessary. U2, W2, and AC8 pins should be left unconnected.

Figure 13: 216-Ball FBGA

	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	27	28	29
A	DNU	V _{SS}	V _{DD2}	DQ30	DQ29	V _{SSQ}	DQ26	DQ25	V _{SSQ}	DQS#3	V _{SSQ}	DQ14	DQ13	V _{SS}	V _{DD1}	V _{DD2}	DQ11	DQ10	DQ9	DQS1	DM1	V _{DDQ}	DQS0	DQ7	DQ6	DQ4	DQ3	V _{SS}	DNU
B	V _{SSQ}	NC	DQ31	V _{DDQ}	DQ28	DQ27	V _{DDQ}	DQ24	V _{DDQ}	DQS3	DM3	DQ15	V _{DDQ}	V _{SSQ}	V _{REFDQ}	V _{DD2}	DQ12	V _{DDQ}	DQ8	DQS#1	V _{SSQ}	DM0	DQS#0	V _{SSQ}	V _{DDQ}	DQ5	DQ2	NC	V _{SSQ}
C	V _{DD1}	DQ16																									V _{DD1}	V _{DD2}	
D	DQ17	V _{DDQ}																									DQ1	V _{DDQ}	
E	DQ18	DQ19																									V _{SSQ}	DQ0	
F	V _{SSQ}	DQ20																									DM2	V _{DDQ}	
G	DQ21	V _{DDQ}																									DQS2	DQS#2	
H	DQ22	DQ23																									V _{SSQ}	DQ23	
J	V _{SSQ}	V _{DDQ}																									V _{DDQ}	DQ22	
K	DQS#2	DQS2																									DQ20	DQ21	
L	DM2	DQ0																									DQ19	V _{SSQ}	
M	DQ1	V _{SSQ}																									V _{DDQ}	DQ18	
N	DQ2	V _{DD1}																									DQ16	DQ17	
P	V _{SS}	V _{SS}																									V _{DD2}	V _{DD1}	
R	V _{DD1}	V _{REFDQ}																									V _{SS}	CA0	
T	V _{DD2}	V _{DD2}																									V _{DDCA}	CA1	
U	V _{DDQ}	DQ3																									V _{REFCA}	CA2	
V	DQ4	V _{SSQ}																									V _{SSCA}	CA3	
W	DQ6	DQ5																									CA4	NC	
Y	V _{DDQ}	DQ7																									CS0#	NC	
AA	DQS0	DQS#0																									V _{SSCA}	CKE0	
AB	DM0	V _{SSQ}																									CK	CK#	
AC	V _{DDQ}	DM1																									V _{DDCA}	CA5	
AD	DQS#1	DQS1																									CA7	CA6	
AE	DQ8	V _{SSQ}																									CA8	V _{DDCA}	
AF	DQ9	V _{DDQ}																									V _{SSCA}	CA9	
AG	DQ10	DQ11																									V _{DD2}	ZQ	
AH	V _{SSQ}	V _{DD1}	V _{DD2}	DQ13	V _{SSQ}	DQ15	DM3	DQS3	V _{DDQ}	DQ26	DQ27	V _{DDQ}	DQ28	DQ29	DQ31	V _{DD1}	V _{SSQ}	V _{REFCA}	CA9	V _{SSCA}	CA7	CA6	CK#	V _{DDCA}	CKE0	CS0#	CA3	CA2	CA1
AJ	DNU	V _{SS}	DQ12	V _{DDQ}	DQ14	V _{DDQ}	V _{SSQ}	DQS#3	DQ24	DQ25	V _{SSQ}	DQ28	DQ29	DQ31	V _{DD1}	V _{SS}	ZQ	CA8	V _{DDCA}	CA5	CK	V _{SSCA}	NC	NC	CA4	V _{DDCA}	CA0	V _{SS}	DNU

Top View (ball down)

Note: 1. V_{DDCA} is unnecessary. T28, AC28, AE29, AH22, AJ19, and AJ26 pins should be left unconnected.

Ball Descriptions

The ball/pad description table below is a comprehensive list of signals for the device family. All signals listed may not be supported on this device. See Ball Assignments for information specific to this device.

Table 8: Ball/Pad Descriptions

Symbol	Type	Description
CA[9:0]	Input	Command/address inputs: Provide the command and address inputs according to the command truth table.
CK, CK#	Input	Clock: CK and CK# are differential clock inputs. All CA inputs are sampled on both rising and falling edges of CK. CS and CKE inputs are sampled at the rising edge of CK. AC timings are referenced to clock.
CKE[1:0]	Input	Clock enable: CKE HIGH activates and CKE LOW deactivates the internal clock signals, input buffers, and output drivers. Power-saving modes are entered and exited via CKE transitions. CKE is considered part of the command code. CKE is sampled at the rising edge of CK.
CS[1:0]#	Input	Chip select: CS# is considered part of the command code and is sampled at the rising edge of CK.
DM[3:0]	Input	Input data mask: DM is an input mask signal for write data. Although DM balls are input-only, the DM loading is designed to match that of DQ and DQS balls. DM[3:0] is DM for each of the four data bytes, respectively.
DQ[31:0]	I/O	Data input/output: Bidirectional data bus.
DQS[3:0], DQS[3:0]#	I/O	Data strobe: The data strobe is bidirectional (used for read and write data) and complementary (DQS and DQS#). It is edge-aligned output with read data and centered input with write data. DQS[3:0]/DQS[3:0]# is DQS for each of the four data bytes, respectively.
V _{DDQ}	Supply	DQ power supply: Isolated on the die for improved noise immunity.
V _{SSQ}	Supply	DQ ground: Isolated on the die for improved noise immunity.
V _{DDCA}	Supply	Command/address power supply: Command/address power supply.
V _{SSCA}	Supply	Command/address ground: Isolated on the die for improved noise immunity.
V _{DD1}	Supply	Core power: Supply 1.
V _{DD2}	Supply	Core power: Supply 2.
V _{SS}	Supply	Common ground
V _{REFCA} , V _{REFDQ}	Supply	Reference voltage: V _{REFCA} is reference for command/address input buffers, V _{REFDQ} is reference for DQ input buffers.
ZQ	Reference	External impedance (240 ohm): This signal is used to calibrate the device output impedance.
RFU	-	Reserved for future use: Must be left floating.
DNU	-	Do not use: Must be grounded or left floating.
NC	-	No connect: Not internally connected.
(NC)	-	No connect: Balls indicated as (NC) are no connects, however, they could be connected together internally.